

RGW00TS65

650V 50A Field Stop Trench IGBT

V _{CES}	650V
I _{C (100°C)}	50A
V _{CE(sat) (Typ.)}	1.5V
P_D	254W

● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

PFC

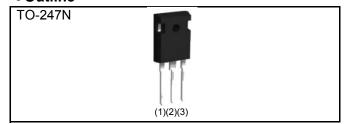
UPS

Welding

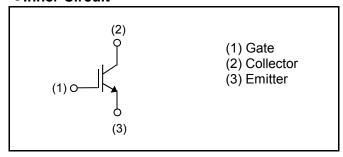
Solar Inverter

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGW00TS65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	T _C = 25°C	I _C	96	А
Collector Current	T _C = 100°C	I _C	50	А
Pulsed Collector Current		I _{CP} *1	200	А
Power Discinction	T _C = 25°C	P _D	254	W
Power Dissipation	T _C = 100°C	P _D	127	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax}.

●Thermal Resistance

Parameter	Symbol	Values			Unit
r ai ai iletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	1	ı	0.59	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai iletei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 33.0 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 50A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.5 1.85	1.9 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Cumbal	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	C _{ies}	V _{CE} = 30V	-	4200	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	104	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	79	-	
Total Gate Charge	Q_g	V _{CE} = 400V	-	141	-	
Gate - Emitter Charge	Q_{ge}	I _C = 50A	-	30	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	52	-	
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	52	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	21	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	180	-	ns
Fall Time	t _f	Inductive Load	-	33	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.18	-	m l
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.96	-	mJ
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	49	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	23	-	
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	201	-	ns
Fall Time	t _f	Inductive Load	-	72	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.18	-	m l
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.18	-	mJ
		I _C = 200A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	ARE	-
		$R_G = 100\Omega, T_j = 175^{\circ}C$				

● Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

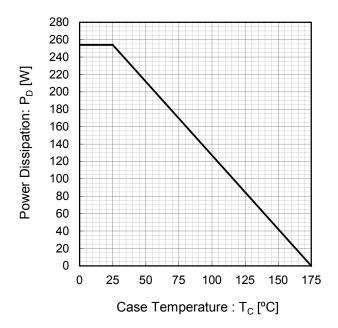


Fig.2 Collector Current vs. Case Temperature

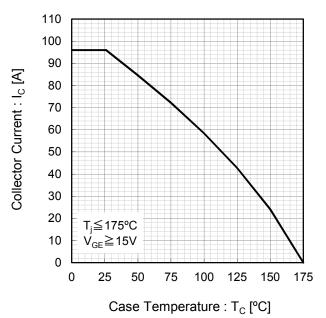


Fig.3 Forward Bias Safe Operating Area

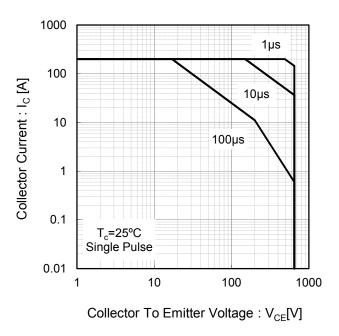
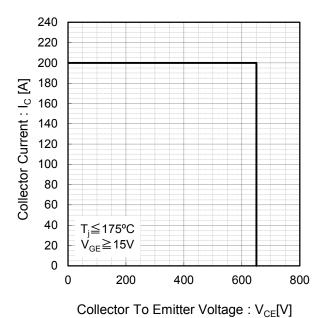


Fig.4 Reverse Bias Safe Operating Area



•Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

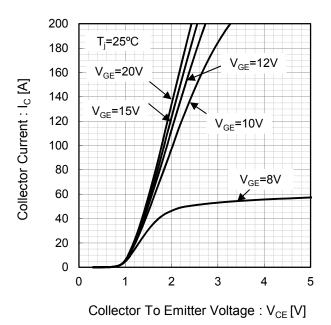
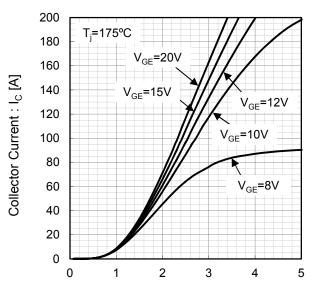


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage: V_{CE}[V]

Fig.7 Typical Transfer Characteristics

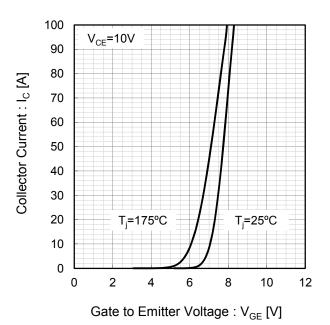
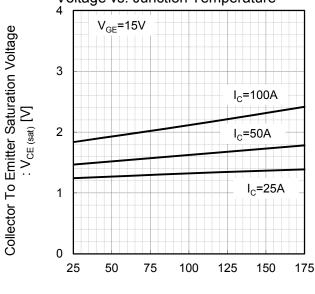


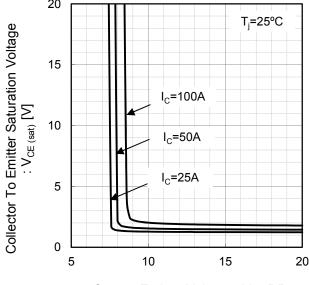
Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

•Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



0

5

Voltage vs. Gate To Emitter Voltage Collector To Emitter Saturation Voltage $: V_{\text{CE (sat)}} \left[V \right]$ T_i=175°C 15 I_C=100A I_C =50A 10 $I_C = 25A$ 5

10

Fig.10 Typical Collector To Emitter Saturation

Gate to Emitter Voltage : V_{GE} [V]

Gate to Emitter Voltage : V_{GE} [V]

15

20

Fig.11 Typical Switching Time vs. Collector Current

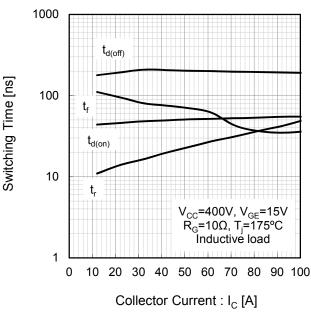
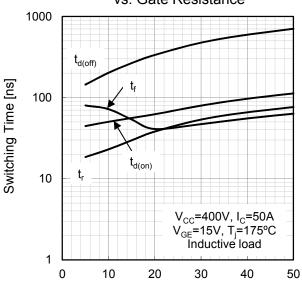


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : R_G [Ω]

•Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

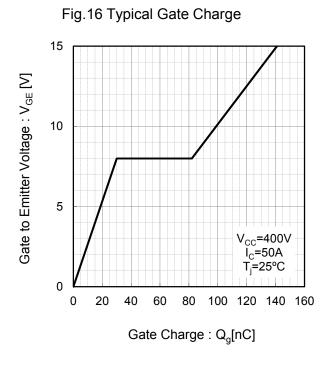
10 E_{off} E_{on} 0.1 $V_{CC}=400V, V_{GE}=15V$ $R_{G}=10\Omega, T_{j}=175^{\circ}C$ Inductive load

0.01 010 20 30 40 50 60 70 80 90 100

Collector Current : I_{C} [A]

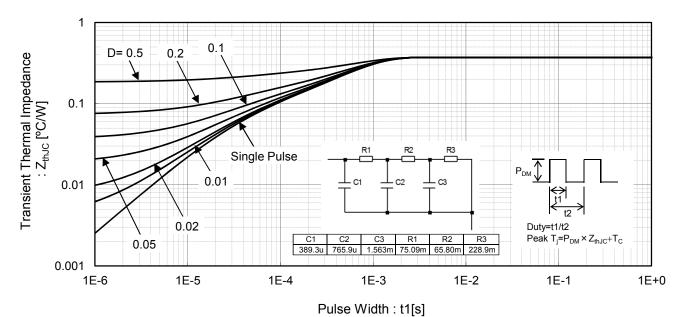
Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 E_{on} 0.1 V_{CC}=400V, I_C=50A V_{GE}=15V, T_j=175°C Inductive load 0.01 10 40 20 30 50 0 Gate Resistance : $R_G [\Omega]$

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V_{GE}=0V -25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : $V_{CE}[V]$



• Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



•Inductive Load Switching Circuit and Waveform

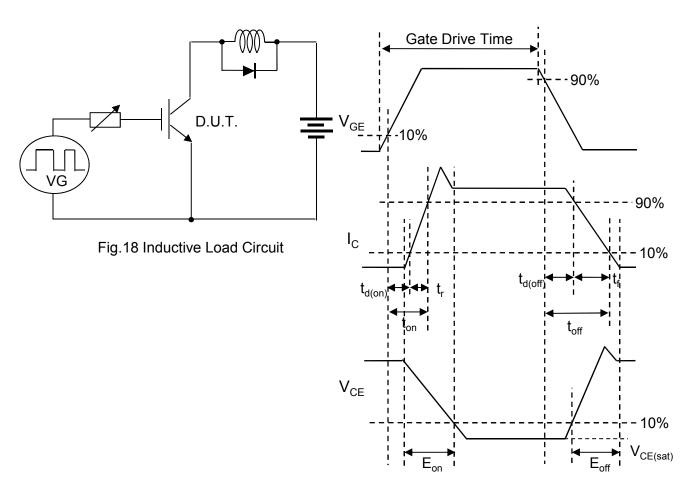


Fig.19 Inductive Load Waveform

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RGW00TS65 - Web Page

Part Number	RGW00TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes